

In the claims:

1. (Currently Amended) A flat panel display, comprising:
 - a flexible substrate;
 - a single crystalline silicon substrate disposed adjacent to the flexible substrate, wherein ~~the flexible substrate is bonded to the single crystalline substrate using an ion implantation process~~ bonding between the flexible substrate and the single crystalline silicon substrate is induced by an ion implantation process through the flexible substrate to an interface of the flexible substrate and the single crystalline silicon substrate; and
 - a plurality of semiconductor devices formed on the single crystalline silicon substrate.
2. (Original) The flat panel display of claim 1, wherein the ion implantation process uses a noble gas.
3. (Original) The flat panel display of claim 1, wherein the ion implantation process uses a gas selected from the group consisting of hydrogen, helium, xenon, and krypton.
4. (Original) The flat panel display of claim 1, wherein the flexible substrate includes a polymer material.
5. (Original) The flat panel display of claim 1, wherein the flexible substrate includes a material selected from the group consisting of polymer, plastic, paper, flexible glass, and stainless steel.
6. (Original) The flat panel display of claim 1, wherein the plurality of semiconductor devices includes thin film transistors.
7. (Original) The flat panel display of claim 1, wherein the ion implantation process includes an ion cut process.
8. (Currently Amended) An electronic device, comprising:

a flexible substrate;

a single crystalline silicon substrate disposed adjacent to the flexible substrate, wherein ~~the flexible substrate is bonded to the single crystalline substrate using an ion implantation process~~ bonding between the flexible substrate and the single crystalline silicon substrate is induced by an ion implantation process through the flexible substrate to an interface of the flexible substrate and the single crystalline silicon substrate; and

a plurality of active semiconductor devices formed on the single crystalline silicon substrate.

9. (Original) The electronic device of claim 8, wherein the ion implantation process uses a noble gas.

10. (Original) The electronic device of claim 8, wherein the ion implantation process uses a gas selected from the group consisting of hydrogen, helium, xenon, and krypton.

11. (Original) The electronic device of claim 8, wherein the flexible substrate includes a polymer material.

12. (Original) The electronic device of claim 8, wherein the flexible substrate includes a material selected from the group consisting of polymer, plastic, paper, flexible glass, and stainless steel.

13. (Original) The electronic device of claim 8, wherein the plurality of active semiconductor devices includes thin film transistors.

14. (Currently Amended) An electronic apparatus, comprising:

a flexible substrate;

a single crystalline silicon substrate disposed adjacent to the flexible substrate, wherein ~~the flexible substrate is bonded to the single crystalline substrate using an ion~~

implantation process bonding between the flexible substrate and the single crystalline silicon substrate is induced by an ion implantation process through the flexible substrate to an interface of the flexible substrate and the single crystalline silicon substrate; and

a plurality of semiconductor devices formed on the single crystalline silicon substrate.

15. (Original) The electronic apparatus of claim 14, wherein the electronic apparatus is a flexible flat panel display.

16. (Original) The electronic apparatus of claim 14, wherein the electronic apparatus is a flexible printed circuit board.

17. (Original) The electronic apparatus of claim 14, wherein the ion implantation process uses a noble gas.

18. (Original) The electronic apparatus of claim 14, wherein the ion implantation process uses a gas selected from the group consisting of hydrogen, helium, xenon, and krypton.

19. (Original) The electronic apparatus of claim 14, wherein the flexible substrate includes a polymer material.

20. (Original) The electronic apparatus of claim 14, wherein the flexible substrate includes a material selected from the group consisting of polymer, plastic, paper, flexible glass, and stainless steel.

21. (Original) The electronic apparatus of claim 14, wherein the plurality of semiconductor devices includes thin film transistors.

22. (Currently Amended) A method of forming an electronic apparatus, comprising:

providing a flexible substrate;

providing a single crystalline silicon substrate disposed adjacent to the flexible substrate, wherein the flexible substrate is bonded to the single crystalline substrate ~~using an~~

~~ion implantation process~~ by an ion implantation process through the flexible substrate to an interface of the flexible substrate and the single crystalline silicon substrate; and

providing a plurality of semiconductor devices formed on the single crystalline silicon substrate.

23. (Original) The method of claim 22, wherein the electronic apparatus is a flexible flat panel display.

24. (Original) The method of claim 22, wherein the electronic apparatus is a flexible printed circuit board.

25. (Original) The method of claim 22, wherein the ion implantation process uses a noble gas.

26. (Original) The method of claim 22, wherein the ion implantation process uses a gas selected from the group consisting of hydrogen, helium, xenon, and krypton.

27. (Original) The method of claim 22, wherein the flexible substrate includes a polymer material.

28. (Original) The method of claim 22, wherein the flexible substrate includes a material selected from the group consisting of polymer, plastic, paper, flexible glass, and stainless steel.

29. (Original) The method of claim 22, wherein the plurality of semiconductor devices includes thin film transistors.